

## Features

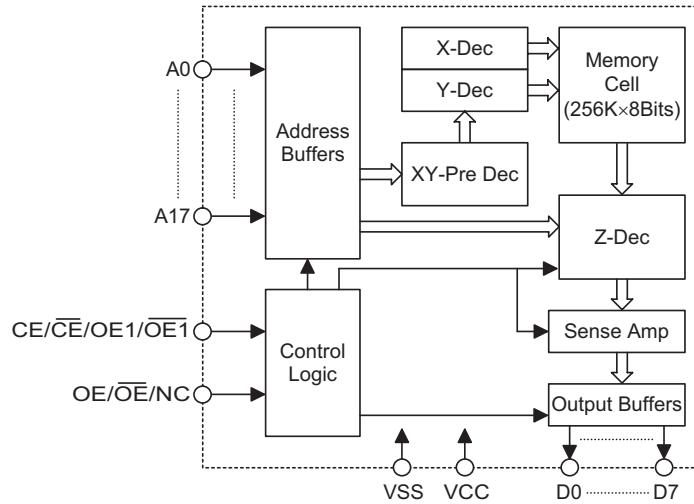
- Operating voltage 2.7V~5.5V
- Low power consumption
  - Operation: 25mA max. ( $V_{CC}=5V$ )  
10mA max. ( $V_{CC}=3V$ )
  - Standby: 30 $\mu$ A max. ( $V_{CC}=5V$ )  
10 $\mu$ A max. ( $V_{CC}=3V$ )
- Access time: 150ns max. ( $V_{CC}=5V$ )  
250ns max. ( $V_{CC}=3V$ )
- 262144×8-bit of mask ROM
- Mask options: chip enable  $CE/\bar{CE}/OE1/\bar{OE}1$  and output enable  $OE/\bar{OE}/NC$
- TTL compatible inputs and outputs
- Tristate outputs
- Fully static operation
- 32-pin DIP/SOP/PLCC package

## General Description

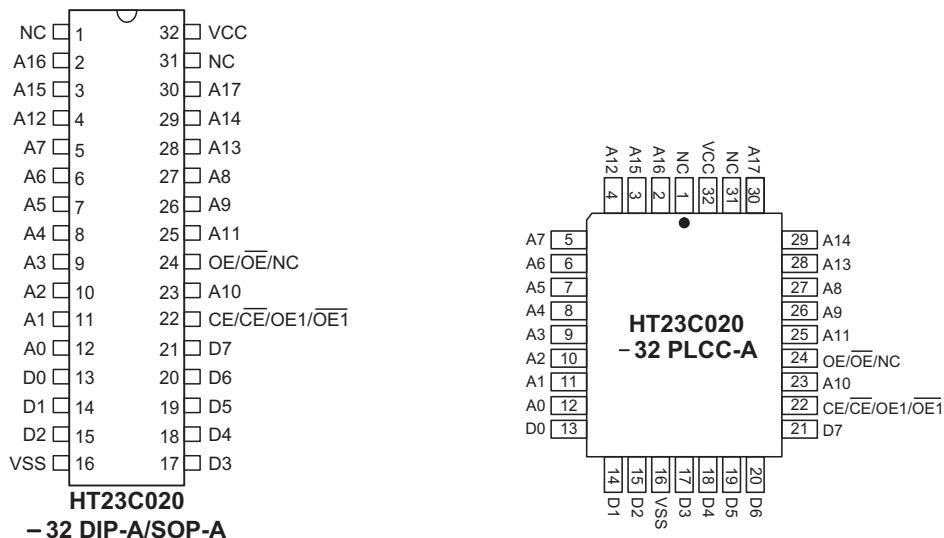
The HT23C020 is a read-only memory with high performance CMOS storage device whose 2048K of memory is arranged into 262144 words by 8 bits.

For application flexibility, the chip enable and output enable control pins can be selected as active high or active low. This flexibility not only allows easy interface with most microprocessors, but also eliminates bus contention in multiple bus microprocessor systems. An additional feature of the HT23C020 is its ability to enter the standby mode whenever the chip enable ( $CE/\bar{CE}$ ) is inactive, thus reducing current consumption to below 30 $\mu$ A. The combination of these functions make the chip suitable for high density low power memory applications.

## Block Diagram



## Pin Assignment



## Pin Description

Pin Name	I/O	Description
A0~A17	I	Address inputs
D0~D7	O	Data outputs
CE/Œ/Œ1/Œ1	I	Chip enable, output enable input
VSS	—	Power supply, ground
VCC	—	Positive power supply
OE/Œ/NC	I	Output enable input
NC	—	No connection

## Absolute Maximum Ratings

Supply Voltage .....  $V_{SS} - 0.3V$  to  $V_{SS} + 6V$       Storage Temperature .....  $-50^{\circ}C$  to  $125^{\circ}C$   
 Input Voltage .....  $V_{SS} - 0.3V$  to  $V_{CC} + 0.3V$       Operating Temperature .....  $-40^{\circ}C$  to  $85^{\circ}C$

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

**D.C. Characteristics**

Ta=−40°C to 85°C

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V <sub>CC</sub>	Conditions				
<b>Supply Voltage: 2.7V~3.6V</b>							
V <sub>CC</sub>	Operating Voltage	—	—	2.7	—	3.6	V
I <sub>CC</sub>	Operating Current	3V	O/P Unload, f= 5MHz	—	—	10	mA
V <sub>IL</sub>	Input Low Voltage	3V	—	V <sub>SS</sub>	—	0.4	V
V <sub>IH</sub>	Input High Voltage	3V	—	2.0	—	V <sub>CC</sub>	V
V <sub>OL</sub>	Output Low Voltage	3V	I <sub>OL</sub> =2.1mA	—	—	0.4	V
V <sub>OH</sub>	Output High Voltage	3V	I <sub>OH</sub> =−0.4mA	2.4	—	V <sub>CC</sub>	V
I <sub>LI</sub>	Input Leakage Current	3V	V <sub>IN</sub> =0 to V <sub>CC</sub>	—	—	10	μA
I <sub>LO</sub>	Output Leakage Current	3V	V <sub>OUT</sub> =0 to V <sub>CC</sub>	—	—	10	μA
I <sub>STB1</sub>	Standby Current	3V	CE=V <sub>IL</sub> , $\overline{CE}=V_{IH}$	—	—	500	μA
I <sub>STB2</sub>	Standby Current	3V	CE ≤ 0.2V, $\overline{CE} ≥ V_{CC}-0.2V$	—	—	10	μA
C <sub>IN</sub>	Input Capacitance (See Note)	—	f=1MHz	—	—	10	pF
C <sub>OUT</sub>	Output Capacitance (See Note)	—	f=1MHz	—	—	10	pF
<b>Supply Voltage: 4.5V~5.5V</b>							
V <sub>CC</sub>	Operating Voltage	—	—	4.5	—	5.5	V
I <sub>CC</sub>	Operating Current	5V	O/P Unload, f=5MHz	—	—	25	mA
V <sub>IL</sub>	Input Low Voltage	5V	—	V <sub>SS</sub>	—	0.8	V
V <sub>IH</sub>	Input High Voltage	5V	—	2.2	—	V <sub>CC</sub>	V
V <sub>OL</sub>	Output Low Voltage	5V	I <sub>OL</sub> =3.2mA	—	—	0.4	V
V <sub>OH</sub>	Output High Voltage	5V	I <sub>OH</sub> =−1mA	2.4	—	V <sub>CC</sub>	V
I <sub>LI</sub>	Input Leakage Current	5V	V <sub>IN</sub> =0 to V <sub>CC</sub>	—	—	10	μA
I <sub>LO</sub>	Output Leakage Current	5V	V <sub>OUT</sub> =0 to V <sub>CC</sub>	—	—	10	μA
I <sub>STB1</sub>	Standby Current	5V	CE=V <sub>IL</sub> , $\overline{CE}=V_{IH}$	—	—	1.5	mA
I <sub>STB2</sub>	Standby Current	5V	CE ≤ 0.2V, $\overline{CE} ≥ V_{CC}-0.2V$	—	—	30	μA
C <sub>IN</sub>	Input Capacitance (See Note)	—	f=1MHz	—	—	10	pF
C <sub>OUT</sub>	Output Capacitance (See Note)	—	f=1MHz	—	—	10	pF

Note: These parameters are periodically sampled but not 100% tested.

**A.C. Characteristics**

Ta=−40°C to 85°C

Symbol	Parameter	V <sub>CC</sub> =2.7V~3.6V		V <sub>CC</sub> =4.5V~5.5V		Unit
		Min.	Max.	Min.	Max.	
t <sub>CYC</sub>	Cycle Time	250	—	150	—	ns
t <sub>AA</sub>	Address Access Time	—	250	—	150	ns
t <sub>ACE</sub>	Chip Enable Access Time	—	250	—	150	ns
t <sub>AOE</sub>	Output Enable Access Time	—	150	—	80	ns
t <sub>OH</sub>	Output Hold Time	—	—	10	—	ns
t <sub>OD</sub>	Output Disable Time (See Note)	—	—	—	70	ns
t <sub>OE</sub>	Output Enable Time (See Note)	—	—	10	—	ns

Note: These parameters are periodically sampled but not 100% tested.

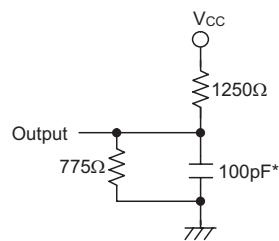
### A.C. Test Conditions

Output load: see figure right

Input rise and fall time: 10ns

Input pulse levels: 0.4V to 2.4V

Input and output timing reference levels:  
0.8V and 2.0V ( $V_{CC}=5V$ ), 1.5V ( $V_{CC}=3V$ )



\* Including scope and jig

**Output Load Circuit**

### Functional Description

The HT23C020 has two modes, namely data read mode and standby mode, controlled by  $\overline{CE}/\overline{CE}$ / $\overline{OE}/\overline{OE}$  and  $OE/\overline{OE}/NC$  inputs.

- **Standby mode**

The HT23C020 has lower current consumption, controlled by the chip enable input ( $\overline{CE}/\overline{CE}$ ). When a low/high level is applied to the  $\overline{CE}/\overline{CE}$  input, regardless of the output enable ( $OE/\overline{OE}/NC$ ) states, the chip will enter the standby mode.

- **Data read mode**

When both the chip enable ( $\overline{CE}/\overline{CE}/\overline{OE}/\overline{OE}$ ) and the output enable ( $OE/\overline{OE}/NC$ ) are active, the chip is in data read mode. Otherwise, active  $\overline{CE}/\overline{CE}$  and inactive  $OE/\overline{OE}/NC$  result in deselect mode. The output will remain in Hi-Z state.

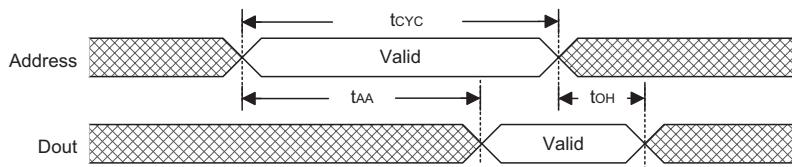
### Operation Truth Table

Mode	$\overline{CE}/\overline{CE}$	$\overline{OE}/\overline{OE}$	$A0 \sim A17$	$D0 \sim D7$
Read	H/L	H/L	Valid	Data Out
Deselect	H/L	L/H	X	High Z
Standby	L/H	X	X	High Z

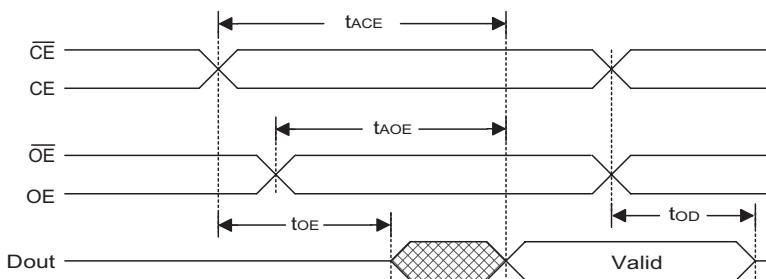
Note: H= $V_{IH}$ , L= $V_{IL}$ , X= $V_{IH}$  or  $V_{IL}$

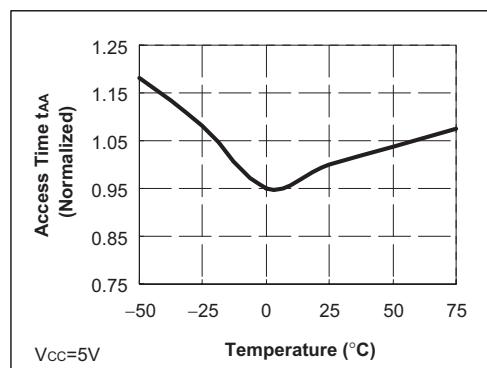
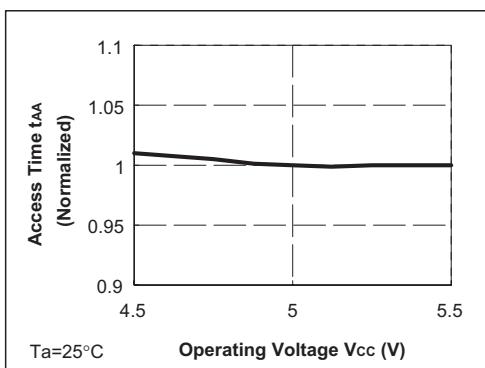
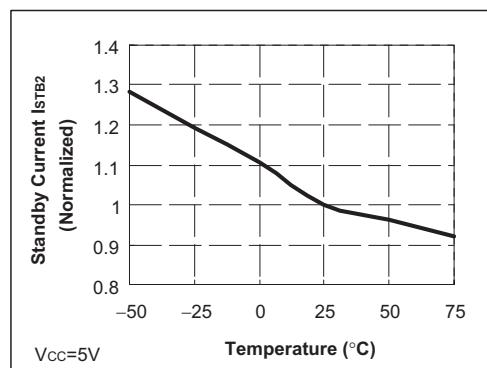
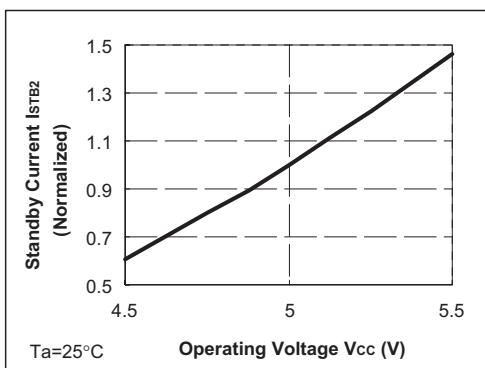
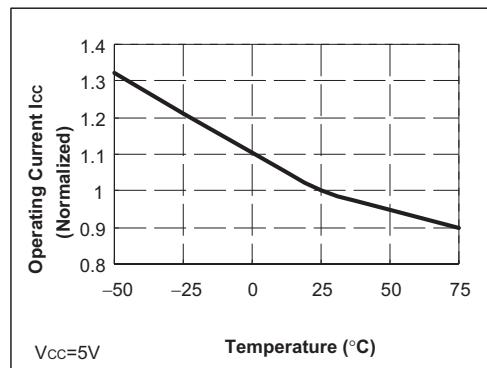
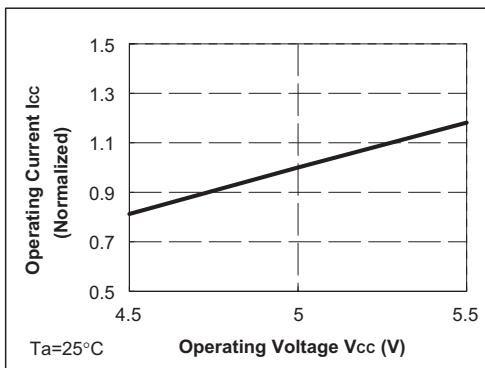
### Timing Diagrams

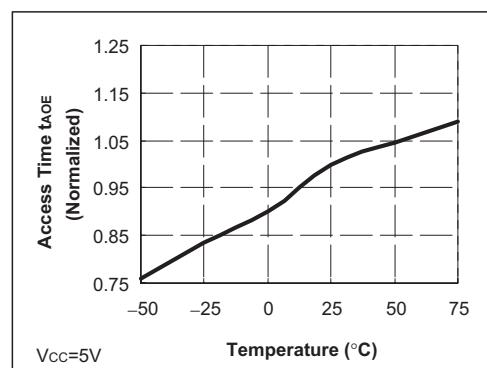
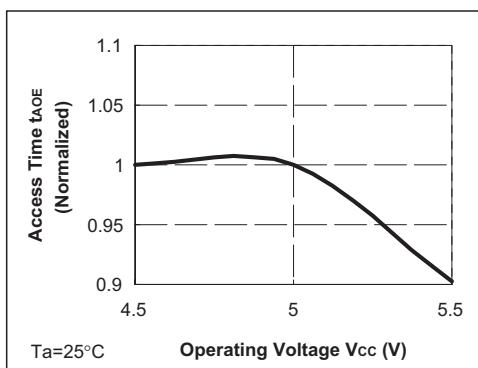
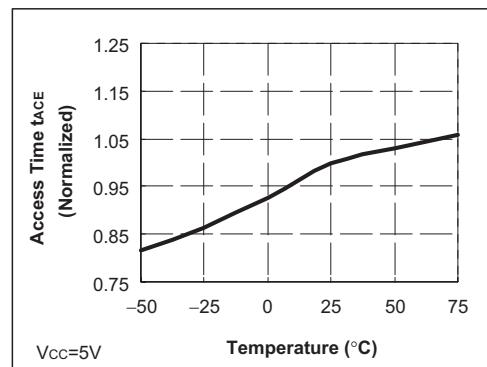
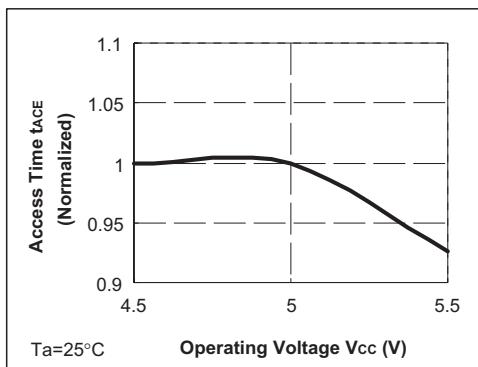
- Propagation Delay Due to Address ( $\overline{CE}/\overline{CE}/\overline{OE}/\overline{OE}$  and  $OE/\overline{OE}$  are Active)



- Propagation Delay Due to Chip and Output Enable (Address Valid)



**Characteristic Curves**




## HT23C020 MASK ROM ORDERING SHEET

Custom: \_\_\_\_\_

but Medium

EPROM

DISK

File (Mail Address: romfile@holtek.com.tw)

OTHER \_\_\_\_\_

User No	Type/Ref. Name	Q'ty	Check Sum	Memory Address	
				Start	End

**Control Pin and Package Form Option:**

- (a) 32 Pin Type Pin 22: \_\_\_\_\_ (1) CE (2)  $\overline{CE}$  (3) OE1 (4)  $\overline{OE1}$   
 Pin 24: \_\_\_\_\_ (1) OE (2)  $\overline{OE}$  (3) NC  
 (b) Package Form: \_\_\_\_\_ (1) Chip Form (2) 32 DIP (3) 32 SOP (4) 32 PLCC

Companion User No. \_\_\_\_\_

Package Marking : \_\_\_\_\_

Delivery Date : \_\_\_\_\_ Q'ty: \_\_\_\_\_

CUSTOM CONFIRMED BY:

\_\_\_\_\_  
(NAME, DATE, POSITION & CO. CHOP)

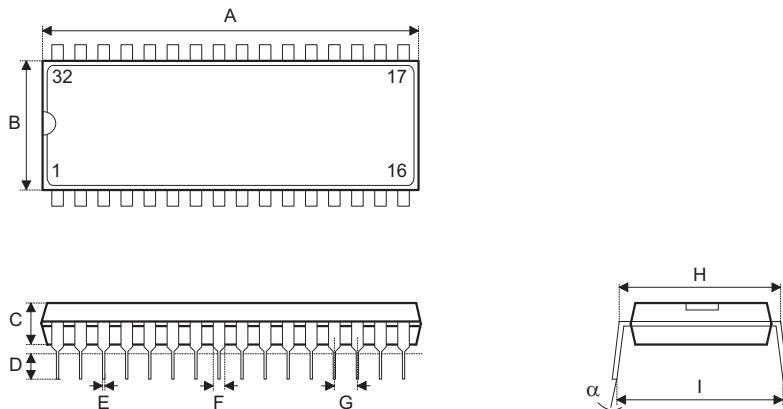
HOLTEK CONFIRMED BY:

\_\_\_\_\_  
(SALES)

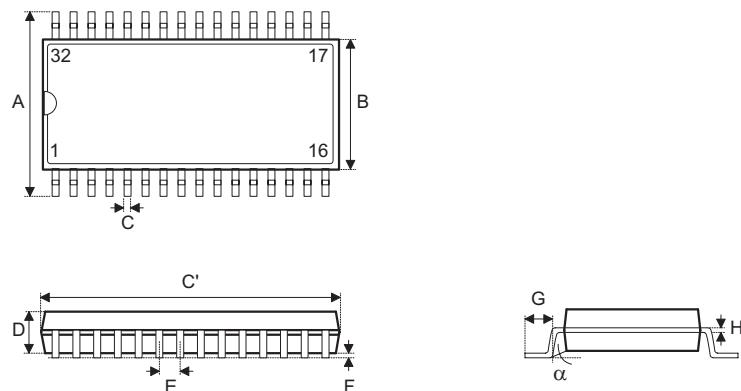
\_\_\_\_\_  
(SALES MANAGER)

### Package Information

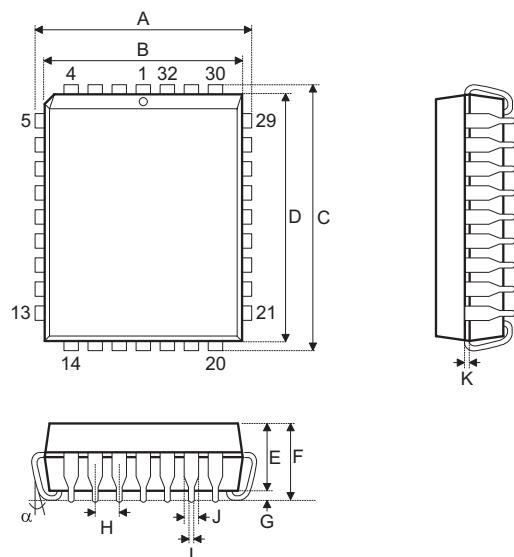
32-pin DIP (600mil) Outline Dimensions



Symbol	Dimensions in mil		
	Min.	Nom.	Max.
A	1635	—	1665
B	535	—	555
C	145	—	155
D	125	—	145
E	16	—	20
F	50	—	70
G	—	100	—
H	595	—	615
I	635	—	670
$\alpha$	0°	—	15°

**32-pin SOP (450mil) Outline Dimensions**


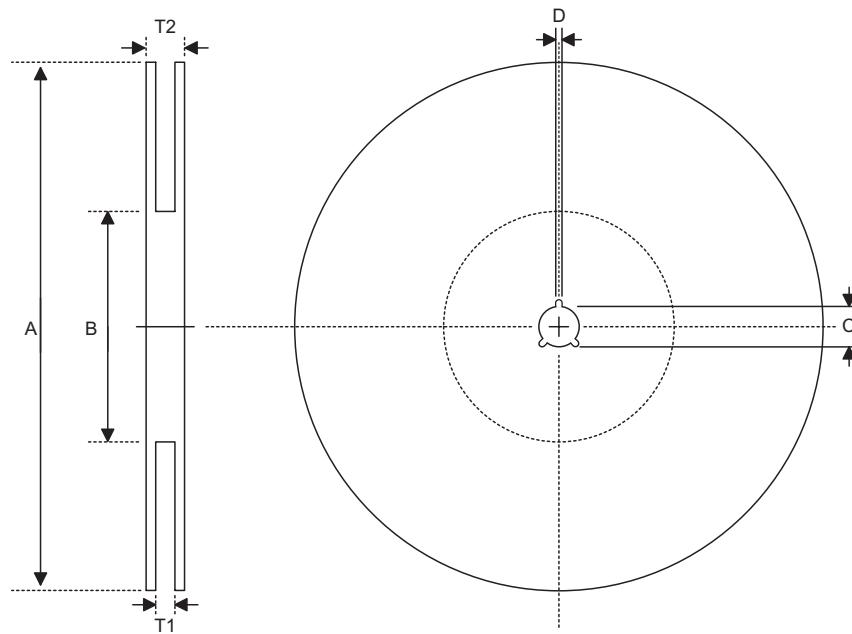
Symbol	Dimensions in mil		
	Min.	Nom.	Max.
A	543	—	557
B	440	—	450
C	14	—	20
C'	—	—	817
D	100	—	112
E	—	50	—
F	4	—	—
G	32	—	38
H	4	—	12
α	0°	—	10°

**32-pin PLCC outline dimensions**


Symbol	Dimensions in mil		
	Min.	Nom.	Max.
A	485	—	495
B	445	—	455
C	585	—	595
D	545	—	555
E	105	—	115
F	—	—	140
G	15	—	—
H	—	50	—
I	16	—	22
J	24	—	32
K	8	—	12
α	0°	—	10°

## Product Tape and Reel Specifications

### Reel Dimensions

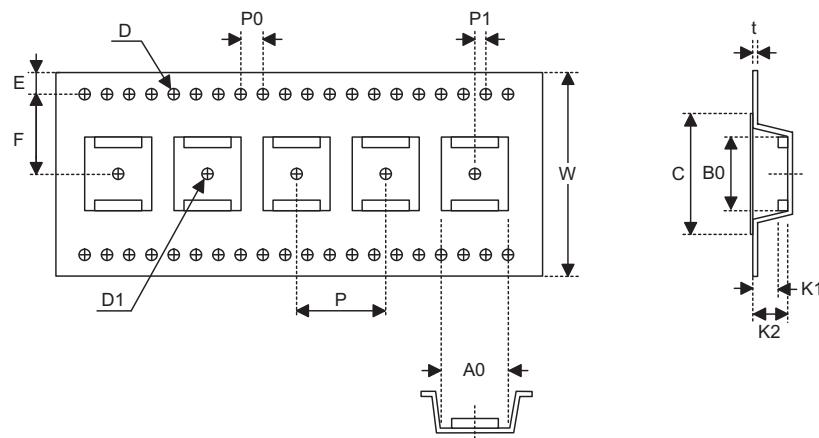


SOP 32W

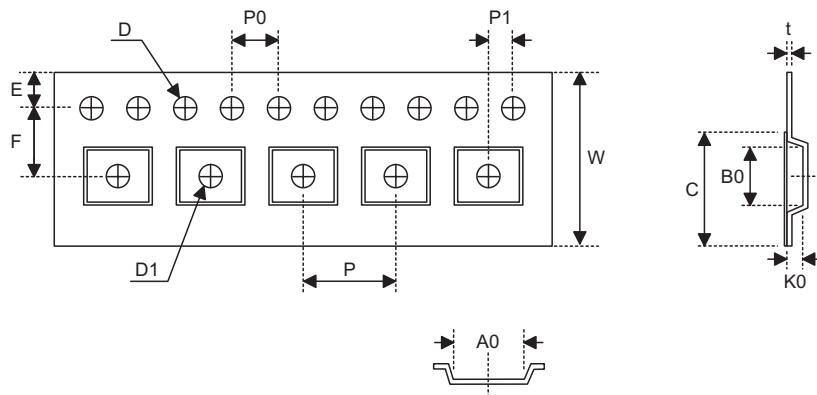
Symbol	Description	Dimensions in mm
A	Reel Outer Diameter	330±1.0
B	Reel Inner Diameter	100±0.1
C	Spindle Hole Diameter	13.0+0.5 -0.2
D	Key Slit Width	2.0±0.5
T1	Space Between Flange	32.8+0.3 -0.2
T2	Reel Thickness	38.2+0.2

PLCC 32

Symbol	Description	Dimensions in mm
A	Reel Outer Diameter	330±1.0
B	Reel Inner Diameter	62±1.5
C	Spindle Hole Diameter	13.0+0.5 -0.2
D	Key Slit Width	2.0±0.5
T1	Space Between Flange	24.8+0.3 -0.2
T2	Reel Thickness	30.2±0.2

**Carrier Tape Dimensions**

**SOP 32W**

<b>Symbol</b>	<b>Description</b>	<b>Dimensions in mm</b>
W	Carrier Tape Width	32.0±0.3 -0.1
P	Cavity Pitch	16.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	14.2±0.1
D	Perforation Diameter	1.55±0.1
D1	Cavity Hole Diameter	2.0±0.25
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.1
A0	Cavity Length	14.7±0.1
B0	Cavity Width	20.9±0.1
K1	Cavity Depth	3.0±0.1
K2	Cavity Depth	3.4±0.1
t	Carrier Tape Thickness	0.35±0.05
C	Cover Tape Width	25.5


**PLCC 32**

<b>Symbol</b>	<b>Description</b>	<b>Dimensions in mm</b>
W	Carrier Tape Width	24.0±0.3
P	Cavity Pitch	18.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	11.5±0.1
D	Perforation Diameter	1.5±0.1
D1	Cavity Hole Diameter	1.55±1.0 -0.05
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.1
A0	Cavity Length	13.1±0.1
B0	Cavity Width	15.5±0.1
K0	Cavity Depth	3.9±0.1
t	Carrier Tape Thickness	0.30±0.05
C	Cover Tape Width	21.3

**Holtek Semiconductor Inc. (Headquarters)**  
No.3, Creation Rd. II, Science Park, Hsinchu, Taiwan  
Tel: 886-3-563-1999  
Fax: 886-3-563-1189  
<http://www.holtek.com.tw>

**Holtek Semiconductor Inc. (Taipei Sales Office)**  
4F-2, No. 3-2, YuanQu St., Nankang Software Park, Taipei 115, Taiwan  
Tel: 886-2-2655-7070  
Fax: 886-2-2655-7373  
Fax: 886-2-2655-7383 (International sales hotline)

**Holtek Semiconductor Inc. (Shanghai Sales Office)**  
7th Floor, Building 2, No.889, Yi Shan Rd., Shanghai, China 200233  
Tel: 021-6485-5560  
Fax: 021-6485-0313  
<http://www.holtek.com.cn>

**Holtek Semiconductor Inc. (Shenzhen Sales Office)**  
43F, SEG Plaza, Shen Nan Zhong Road, Shenzhen, China 518031  
Tel: 0755-8346-5589  
Fax: 0755-8346-5590  
ISDN: 0755-8346-5591

**Holtek Semiconductor Inc. (Beijing Sales Office)**  
Suite 1721, Jinyu Tower, A129 West Xuan Wu Men Street, Xicheng District, Beijing, China 100031  
Tel: 010-6641-0030, 6641-7751, 6641-7752  
Fax: 010-6641-0125

**Holmate Semiconductor, Inc. (North America Sales Office)**  
46712 Fremont Blvd., Fremont, CA 94538  
Tel: 510-252-9880  
Fax: 510-252-9885  
<http://www.holmate.com>

Copyright © 2003 by HOLTEK SEMICONDUCTOR INC.

The information appearing in this Data Sheet is believed to be accurate at the time of publication. However, Holtek assumes no responsibility arising from the use of the specifications described. The applications mentioned herein are used solely for the purpose of illustration and Holtek makes no warranty or representation that such applications will be suitable without further modification, nor recommends the use of its products for application that may present a risk to human life due to malfunction or otherwise. Holtek's products are not authorized for use as critical components in life support devices or systems. Holtek reserves the right to alter its products without prior notification. For the most up-to-date information, please visit our web site at <http://www.holtek.com.tw>.